

## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims**

#### **Claims 1-13 (Cancelled):**

**Claim 14 (Currently amended):** An impurity introducing method which comprising:

a ~~set~~step of introducing an impurity selected from a group consisting of B, As, P, Sb and In into a surface of a semiconductor substrate; and

a step of radiating inactive plasma to the surface of the semiconductor substrate after the impurity introducing step.

**Claim 15 (Previously presented):** The impurity introducing method according to claim 14, wherein the step of radiating the plasma includes a step of radiating plasma such that the impurity possesses a desired impurity profile in the semiconductor substrate.

**Claim 16 (Previously presented):** The impurity introducing method according to claim 14, wherein the step of radiating the plasma includes a step of radiating plasma which contains at least one kind of rare gas element.

**Claim 17 (Previously presented):** The impurity introducing method according to claim 16, wherein the step of radiating the plasma includes a step of radiating He plasma.

**Claim 18 (Cancelled):**

**Claim 19 (Previously presented):** The impurity introducing method according to claim 14, wherein the step of introducing the impurity includes a plasma-doping step.

**Claim 20 (Previously presented):** The impurity introducing method according to claim 14, wherein the step of introducing the impurity includes an ion-implanting step.

**Claim 21 (Previously presented):** The impurity introducing method according to claim 14, wherein the step of introducing the impurity includes a gas-doping step.

**Claim 22 (Currently amended):** A semiconductor device which is formed by using an impurity introducing method according to claim 14, wherein the semiconductor device is formed to have the

impurity profile in which the impurity concentration at a depth position of 4nm is set to be 1/10 or more of the impurity concentration on a surface of the semiconductor device.

**Claim 23 (Currently amended):** The semiconductor device according to claim 22, wherein the semiconductor device is formed to have the impurity profile in which the impurity concentration at a depth position of 7nm is set to be 1/100 or more of the impurity concentration on the surface of the semiconductor device.